

# DMTH84M1SPSQ

#### 80V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

## **Product Summary**

BV <sub>DSS</sub>	Rds(on)	ID Tc = +25°C (Note 11)	
80V	$4m\Omega \otimes V_{GS} = 10V$	100A	

# **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

PowerDI5060-8

- DC-DC Converters
- Load Switch

Notes:

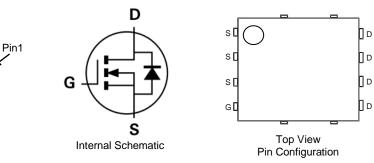


- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low RDS(ON) Minimizes On State Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMTH84M1SPSQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/guality/product-definitions/

#### **Mechanical Data**

- Case: PowerDI<sup>®</sup>5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 🔞
- Weight: 0.097 grams (Approximate)



## Ordering Information (Note 4)

Top View

Part Number	Case	Packaging
DMTH84M1SPSQ-13	PowerDI5060-8	2,500 / Tape & Reel

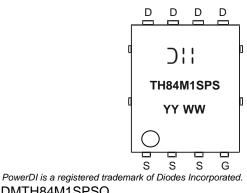
EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Bottom View

## Marking Information



DMTH84M1SPSQ Document number: DS42176 Rev. 2 - 2



#### Maximum Ratings (@Tc = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			VDSS	80	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current, V <sub>GS</sub> = 10V (Note 7)	Steady State	Tc = +25°C Tc = +100°C (Note 11)	D	100 100	A
Maximum Continuous Body Diode Forward Current (I	ls	83	A		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	Ідм	400	A		
Pulsed Body Diode Forward Current (10µs Pulse, Du	Ism	400	A		
Avalanche Current, L = 1mH (Note 8)			I <sub>AS</sub>	23	A
Avalanche Energy, L = 1mH (Note 8)			Eas	264.5	mJ

# Thermal Characteristics (@T<sub>C</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	PD	1.6	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>θJA</sub>	96	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	PD	2.8	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	RθJA	53	°C/W
Total Power Dissipation (Note 7)	Tc = +25°C	PD	136	W
Thermal Resistance, Junction to Case (Note 7)		R <sub>θJC</sub>	1.1	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

### Electrical Characteristics (@T<sub>C</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BVDSS	80	—	—	V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS			1	μA	$V_{DS} = 64V, V_{GS} = 0V$	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)	·						
Gate Threshold Voltage	Vgs(th)	2	—	4	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	Deserve		3.1	4	mΩ	$V_{GS} = 10V, I_D = 20A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	4.4	5.7	11152	VGS = 6V, ID = 20A	
Diode Forward Voltage	Vsd	_	0.8	1.2	V	VGS = 0V, IS = 20A	
DYNAMIC CHARACTERISTICS (Note 10)	·						
Input Capacitance	Ciss	_	4209	—		$V_{DS} = 40V, V_{GS} = 0V,$ f = 1MHz	
Output Capacitance	Coss		1513	—	pF		
Reverse Transfer Capacitance	Crss	_	62	_			
Gate Resistance	Rg	_	2.2	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 6V)	Qg		41	—		V <sub>DS</sub> = 40V, I <sub>D</sub> = 20A	
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg		63	—	nC		
Gate-Source Charge	Qgs	_	17	—	nc		
Gate-Drain Charge	Q <sub>gd</sub>	_	16	_			
Turn-On Delay Time	tD(ON)	_	16	_		$V_{DD} = 40V, V_{GS} = 10V,$ $I_D = 20A, R_G = 6\Omega$	
Turn-On Rise Time	t <sub>R</sub>	_	24	_			
Turn-Off Delay Time	tD(OFF)	_	53	—	ns		
Turn-Off Fall Time	tF	_	31	—			
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	56	_	ns		
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	_	100	_	nC	Is = 20A, di/dt = 100A/µs	

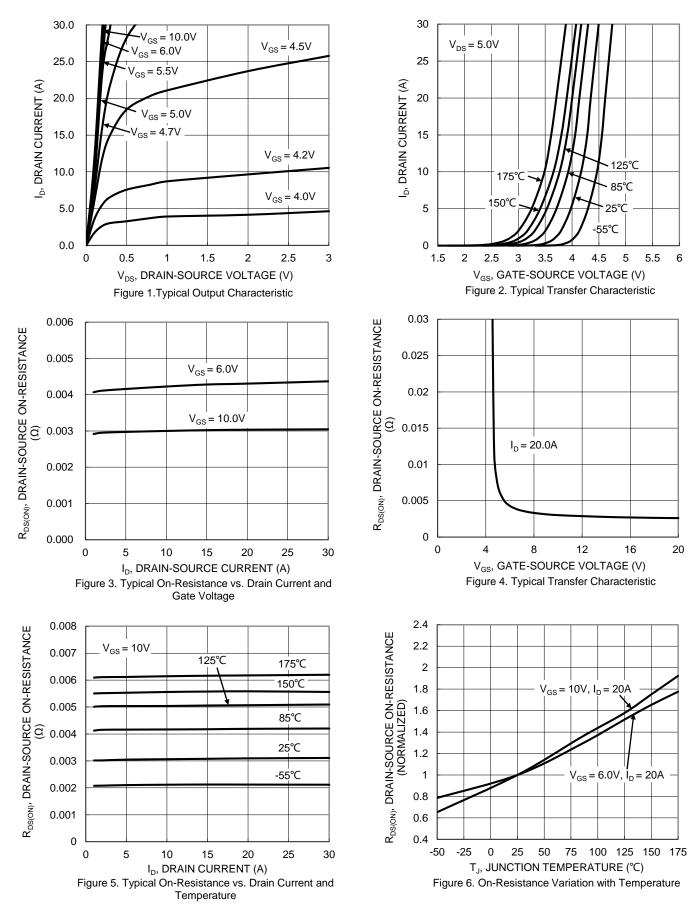
Notes:

Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
Thermal resistance from junction to soldering point (on the exposed drain pad).

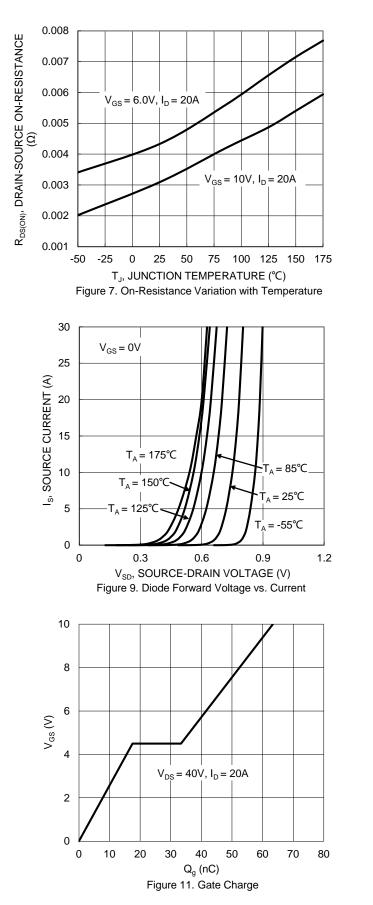
8. I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep  $T_J = +25^{\circ}C$ . 9. Short duration pulse test used to minimize self-heating effect. 10. Guaranteed by design. Not subject to product testing. 11. Package limited.

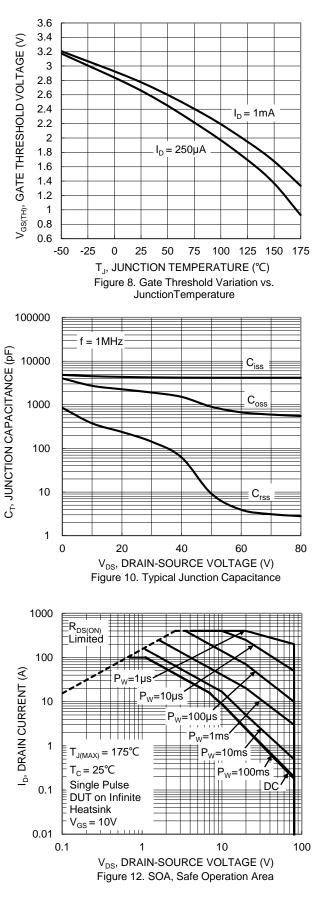


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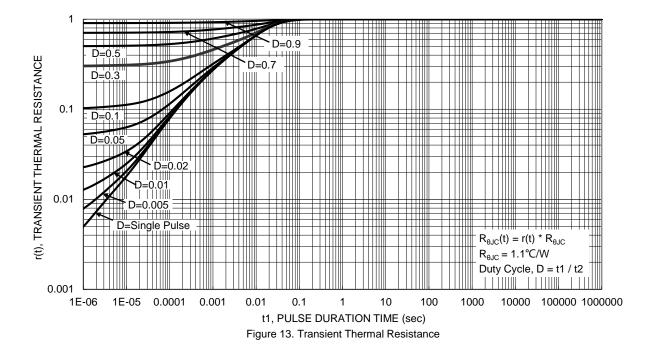






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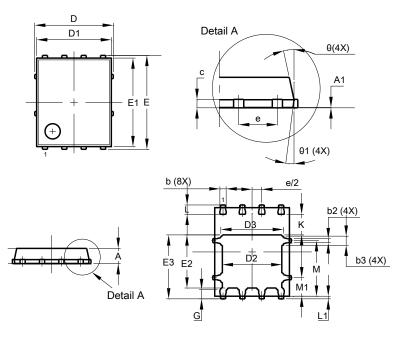




# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8

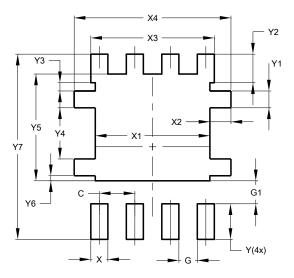


PowerDI5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05	-		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
С	0.230	0.330	0.277		
D		5.15 BSC	;		
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
E	6.15 BSC				
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е	1.27 BSC				
G	0.51	0.71	0.61		
K	0.51	-	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
М	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
Al	All Dimensions in mm				

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610



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